

ETCHANT SOLUTIONS AND METHOD OF USE THEREOF

ABSTRACT OF THE DISCLOSURE

Etching compositions and method of using the etching compositions comprising potassium hydroxide; one or more than one additional alkaline compounds selected
5 from the group consisting of TEAH, TMAF and NH_4OH ; and water; or etching compositions comprising one or more than one inorganic alkali basic hydroxides selected from the group consisting of potassium hydroxide, cesium hydroxide, sodium hydroxide, rubidium hydroxide, or lithium hydroxide; optionally one or more than one
10 additional alkaline compounds; water; and optionally one or more corrosion inhibitors; wherein the composition preferentially etches silicon present on a substrate as compared to silicon dioxide present on said substrate.

Fig. 1